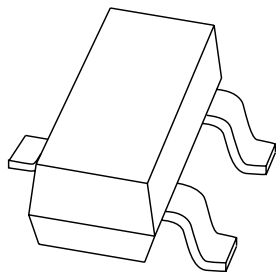


DATA SHEET



PBSS4240T

40 V; 2 A NPN low V_{CEsat}
(BISS) transistor

Product data sheet
Supersedes data of 2001 Jul 13

2004 Jan 09

40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation
- Replacement for SOT89/SOT223 standard packaged transistors.

APPLICATIONS

- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

DESCRIPTION

NPN low V_{CEsat} transistor in a SOT23 plastic package.
PNP complement: PBSS5240T.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS4240T	ZE*

Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

ORDERING INFORMATION

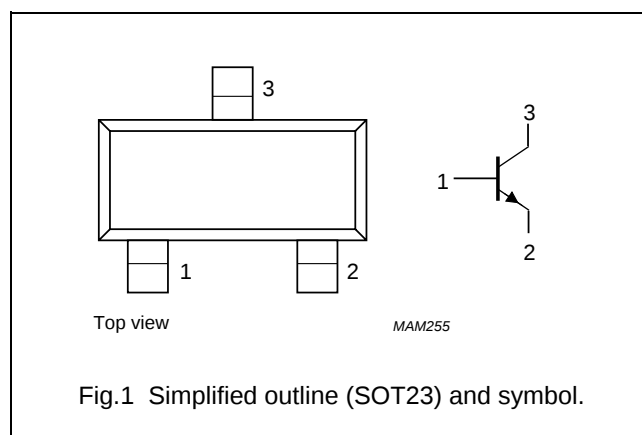
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS4240T	–	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	40	V
I_{CM}	peak collector current	3	A
R_{CEsat}	equivalent on-resistance	<200	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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PBSS4240T

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	2	A
I_{CM}	peak collector current		–	3	A
I_{BM}	peak base current		–	300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$; note 2	–	480	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

Notes

1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 100\text{ mA}; V_{CE} = 2\text{ V}$	350	470	–	
		$I_C = 500\text{ mA}; V_{CE} = 2\text{ V}$	300	450	–	
		$I_C = 1\text{ A}; V_{CE} = 2\text{ V}$	300	420	–	
		$I_C = 2\text{ A}; V_{CE} = 2\text{ V}$	150	250	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	45	70	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	70	100	mV
		$I_C = 750\text{ mA}; I_B = 15\text{ mA}$	–	120	180	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{note 1}$	–	130	180	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	240	320	mV
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	140	<200	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	–	1.1	V
V_{BEon}	base-emitter turn on voltage	$I_C = 100\text{ mA}; V_{CE} = 2\text{ V}$	–	–	0.75	V
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	15	20	pF
f_T	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	230	–	MHz

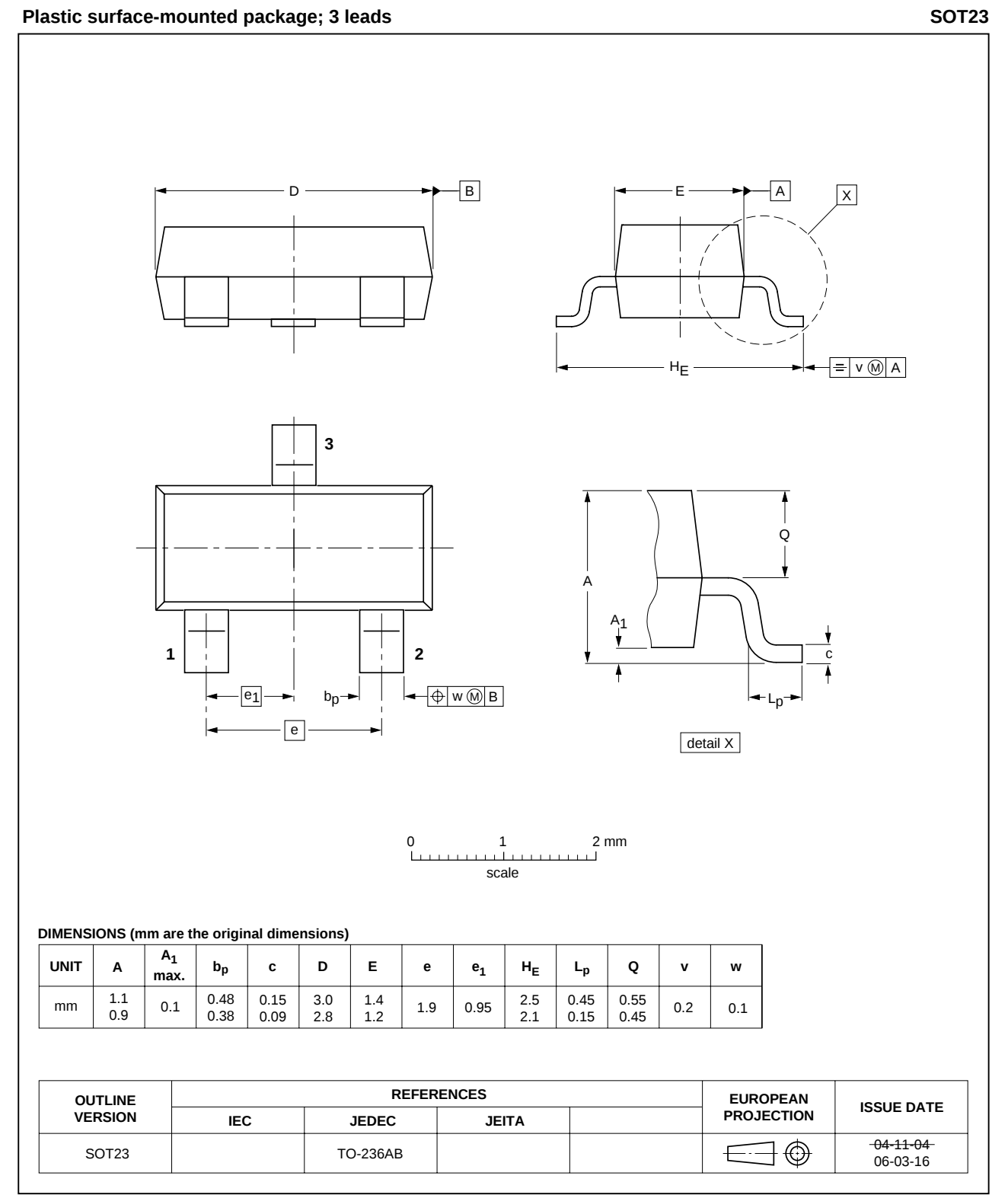
Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

PACKAGE OUTLINE



40 V; 2 A NPN low V_{CEsat} (BISS) transistor

PBSS4240T

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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